# onsemi

# PNP Epitaxial Silicon Transistor

# **FJV992**

### Audio Frequency Low Noise Amplifier

• Complement to FJV1845

### MAXIMUM RATINGS (T<sub>a</sub> = 25°C unless otherwise noted)

Symbol	Rating	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-120	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-120	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
Ι <sub>C</sub>	Collector Current	-50	mA
P <sub>C</sub>	Collector Power Dissipation	300	mW
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### h<sub>FE2</sub> CLASSIFICATION

Classification	Р	F	E
h <sub>FE2</sub>	200 ~ 400	300 ~ 600	400 ~ 800

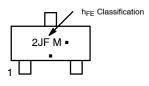
#### ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25°C unless otherwise noted)



Base
Emitter
Collector

SOT-23 (TO-236) CASE 318 STYLE 6

#### MARKING DIAGRAM



2JF = Specific Device Code

M = Assembly Operation Month

= Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
FJV992FMTF	SOT-23 (TO-236)	3000 /
	(Pb-Free)	Tape & Reel

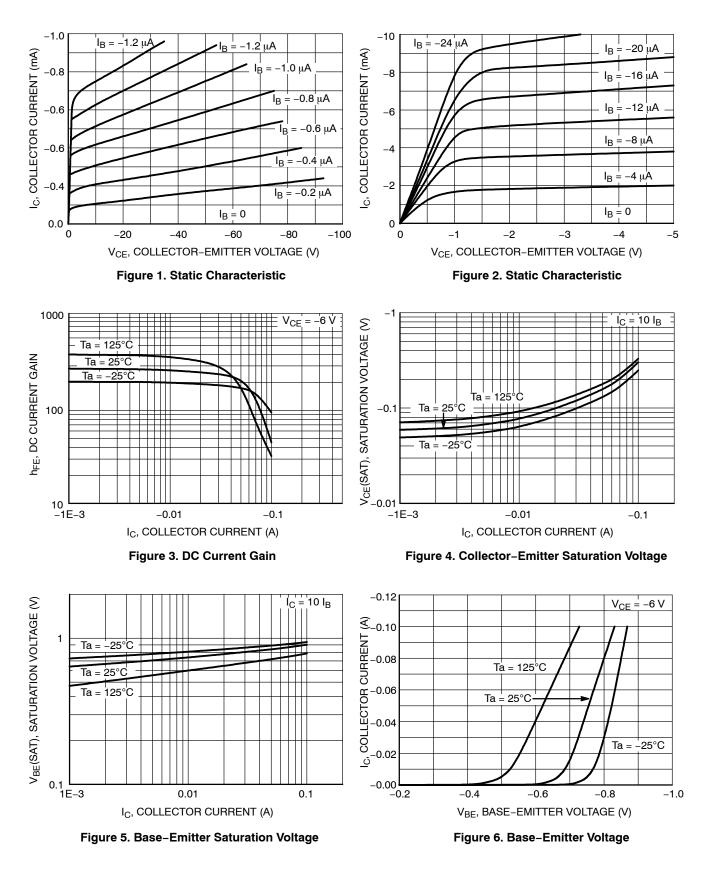
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, <u>BRD8011/D</u>.

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = -100 \ \mu A, \ I_{E} = 0$	-120	_	-	V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = -1  {\rm mA},  I_{\rm B} = 0$	-120	-	-	V
BV <sub>EBO</sub>	Emitter-Emitter Breakdown Voltage	$I_{E} = -10 \ \mu A, \ I_{C} = 0$	-5	-	-	V
I <sub>EBO</sub>	Emitter-Base Cutoff Current	$V_{EB} = -6 V, I_C = 0$	-	-	-30	nA
h <sub>FE1</sub>	DC Current Gain	$V_{CE} = -6 \text{ V}, I_C = -0.1 \text{ mA}$	150	-	-	
h <sub>FE2</sub>		$V_{CE} = -6 \text{ V}, I_{C} = -1 \text{ mA}$	200	-	800	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_{\rm C} = -10$ mA, $I_{\rm B} = -1$ mA	-	-	-300	mV
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE} = -6 \text{ V}, I_{C} = -1 \text{ mA}$	-0.55	-	-0.65	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = -6 \text{ V}, \text{ I}_{C} = -1 \text{ mA}$	50	_	-	MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB} = -30$ V, $I_E = 0$ , f = 1 MHz	-	_	3	pF
NV	Noise Voltage	$\begin{array}{l} V_{CE}=-5.0 \ \text{V}, \ \text{I}_{C}=-1.0 \ \text{mA}, \\ R_{G}=100 \ \text{k}\Omega, \ \text{G}_{V}=80 \ \text{dB}, \\ f=10 \ \text{Hz} \ \text{to} \ 1.0 \ \text{kHz} \end{array}$	-	-	40	mV

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

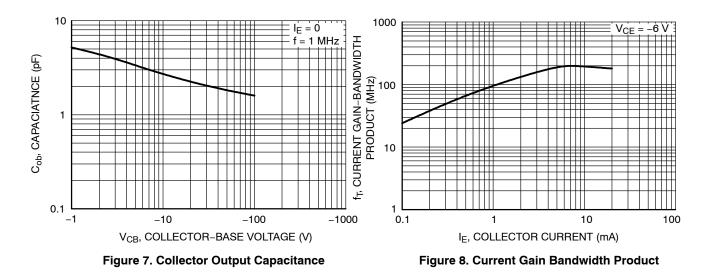
## FJV992

### **TYPICAL CHARACTERISTICS**



# FJV992

## TYPICAL CHARACTERISTICS (continued)



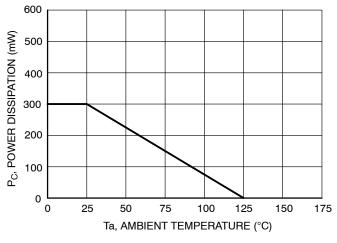


Figure 9. Power Derating

# semi



#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318**

**ISSUE AU** 

DATE 14 AUG 2024













XXX = Specific Device Code М = Date Code

= Pb-Free Package .

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MILLIMETERS						
DIM	MIN	NOM	МАХ			
А	0.89	1.00	1.11			
A1	0.01	0.06	0.10			
b	0.37	0.44	0.50			
с	0.08	0.14	0.20			
D	2.80	2.90	3.04			
E	1.20	1.30	1.40			
е	1.78	1.90	2.04			
L	0.30	0.43	0.55			
L1	0.35	0.54	0.69			
Ηe	2.10	2.40	2.64			
Т	0°		10°			

NOTES:

DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: 1.

2. MILLIMETERS.

MILLIME IERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE 3.

BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, 4. PROTRUSIONS, OR GATE BURRS.

#### RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42226B Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.					
DESCRIPTION: SOT-23 (TO-236) 2.90x1.30x1.00 1.90P PAGE 1 OF 2						
onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights of others.						

© Semiconductor Components Industries, LLC, 2019

#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CÁSE 318** ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	I	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DESCRIPTION: SOT-23 (TO-236) 2.90x1.30x1.00 1.90P PAGE 2 OF 2	DOCUMENT NUMBER:	98ASB42226B	the Document Repository. COPY" in red.	
	DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P		PAGE 2 OF 2

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent\_Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or indental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification. Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs,

#### ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at <u>www.onsemi.com/support/sales</u>

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi:

FJV992PMTF FJV992FMTF